ABSTRACT OF THE DISCLOSURE

SOI substrates are fabricated with sufficient quality and with good reproducibility. At the same time, saving of resources and reduction of cost are realized by reuse of wafer and the like.

Carried out to achieve the above are a step of bonding a principal surface of a first substrate to a principal surface of a second substrate, the first substrate being an Si substrate in which at least one layer of non-porous thin film is formed through a porous Si layer, a step of exposing the porous Si layer in a side surface of a bonding substrate comprised of the first substrate and the second substrate, a step of dividing the porous Si layer by oxidizing the bonding substrate, and a step of removing porous Si and oxidized porous Si layer on the second substrate separated by the division of the porous Si layer.

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